



5STF 13F1220

Old part no. TR 918-1250-12

Fast Thyristor

Properties

- Amplifying gate
- High operational capability
- Optimized turn-off parameters

Applications

- Power switching applications

Key Parameters

V_{DRM}, V_{RRM}	= 1 200	V
I_{TAV}	= 1 252	A
I_{TSM}	= 21.0	kA
V_{TO}	= 1.772	V
r_T	= 0.248	m Ω
t_q	= 20.0	μ s

Types

	V_{RRM}, V_{DRM}
5STF 13F1220	1 200 V
5STF 13F1020	1 000 V

Conditions:
 $T_j = -40 \div 125$ °C, half sine waveform,
 $f = 50$ Hz

Mechanical Data

F_m	Mounting force	22 \pm 2 kN
m	Weight	0.48 kg
D_s	Surface creepage distance	25 mm
D_a	Air strike distance	13 mm

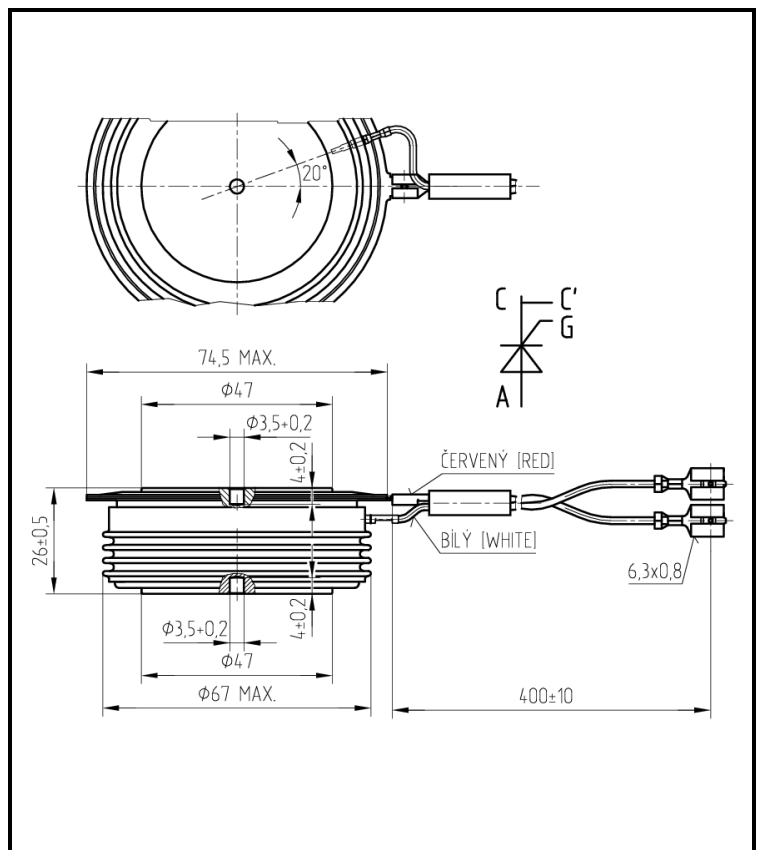


Fig. 1 Case



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Maximum Ratings			Maximum Limits	Unit
V_{RRM} V_{DRM}	Repetitive peak reverse and off-state voltage $T_j = -40 \div 125 \text{ }^\circ\text{C}$	5STF 13F1220 5STF 13F1020	1 200 1 000	V
I_{TRMS}	RMS on-state current $T_c = 70 \text{ }^\circ\text{C}$, half sine waveform, $f = 50 \text{ Hz}$		1 966	A
I_{TAVm}	Average on-state current $T_c = 70 \text{ }^\circ\text{C}$, half sine waveform, $f = 50 \text{ Hz}$		1 252	A
I_{TSM}	Peak non-repetitive surge half sine pulse, $V_R = 0 \text{ V}$	$t_p = 10 \text{ ms}$ $t_p = 8.3 \text{ ms}$	21 000 22 400	A
$\int i^2 t$	Limiting load integral half sine pulse, $V_R = 0 \text{ V}$	$t_p = 10 \text{ ms}$ $t_p = 8.3 \text{ ms}$	2 205 000 2 080 000	A²s
$(di_T/dt)_{cr}$	Critical rate of rise of on-state current $I_T = I_{TAVm}$, half sine waveform, $f = 50 \text{ Hz}$, $V_D = 2/3 V_{DRM}$, $t_r = 0.3 \text{ } \mu\text{s}$, $I_{GT} = 2 \text{ A}$		800	A/μs
$(dv_D/dt)_{cr}$	Critical rate of rise of off-state voltage $V_D = 2/3 V_{DRM}$		1 000	V/μs
P_{GAVm}	Maximum average gate power losses		3	W
I_{FGM}	Peak gate current		10	A
V_{FGM}	Peak gate voltage		12	V
V_{RGM}	Reverse peak gate voltage		10	V
$T_{jmin} - T_{jmax}$	Operating temperature range		-40 \div 125	$^\circ\text{C}$
$T_{stgmin} - T_{stgmax}$	Storage temperature range		-40 \div 125	$^\circ\text{C}$

Unless otherwise specified $T_j = 125 \text{ }^\circ\text{C}$

Characteristics		Value			Unit
		min.	typ.	max.	
V_{TM}	Maximum peak on-state voltage $I_{TM} = 2\ 000\ A$			2.270	V
V_{T0}	Threshold voltage			1.772	V
r_T	Slope resistance $I_{T1} = 1\ 963\ A, I_{T2} = 5\ 890\ A$			0.248	mΩ
I_{DM}	Peak off-state current $V_D = V_{DRM}$			150	mA
I_{RM}	Peak reverse current $V_R = V_{RRM}$			150	mA
t_{gd}	Delay time $T_j = 25\ ^\circ C, V_D = 0.4\ V_{DRM}, I_{TM} = I_{TAVm},$ $t_r = 0.3\ \mu s, I_{GT} = 2\ A$			2.0	μs
t_q	Turn-off time $I_T = 1\ 000\ A, di_T/dt = -50\ A/\mu s, V_R = 100\ V,$ $V_D = 2/3\ V_{DRM}, dv_D/dt = 50\ V/\mu s$			20.0	μs
Q_{rr}	Recovery charge <i>the same conditions as at t_q</i>		200		μC
I_{rrM}	Reverse recovery current <i>the same conditions as at t_q</i>		100		A
I_H	Holding current	$T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$		250 150	mA
I_L	Latching current	$T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$		1 500 1 000	mA
V_{GT}	Gate trigger voltage $V_D = 12\ V, I_T = 4\ A$	$T_j = -40\ ^\circ C$ $T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$	0.25	4 3 2	V
I_{GT}	Gate trigger current $V_D = 12\ V, I_T = 4\ A$	$T_j = -40\ ^\circ C$ $T_j = 25\ ^\circ C$ $T_j = 125\ ^\circ C$	10	500 250 150	mA

Unless otherwise specified $T_j = 125\ ^\circ C$

Thermal Parameters		Value	Unit
R_{thjc}	Thermal resistance junction to case <i>double side cooling</i>	16.0	K/kW
	<i>anode side cooling</i>	25.0	
	<i>cathode side cooling</i>	45.0	
R_{thch}	Thermal resistance case to heatsink <i>double side cooling</i>	4.0	K/kW
	<i>single side cooling</i>	8.0	

Transient Thermal Impedance

Analytical function for transient thermal impedance

$$Z_{thjc} = \sum_{i=1}^4 R_i (1 - \exp(-t / \tau_i))$$

Conditions:

$F_m = 22 \pm 2$ kN, Double side cooled

Correction for periodic waveforms

180° sine:	add 1.3 K/kW
180° rectangular:	add 1.8 K/kW
120° rectangular:	add 3.0 K/kW
60° rectangular:	add 5.1 K/kW

i	1	2	3	4
τ_i (s)	0.4653	0.1533	0.0375	0.0034
R_i (K/kW)	5.50	7.24	2.00	1.34

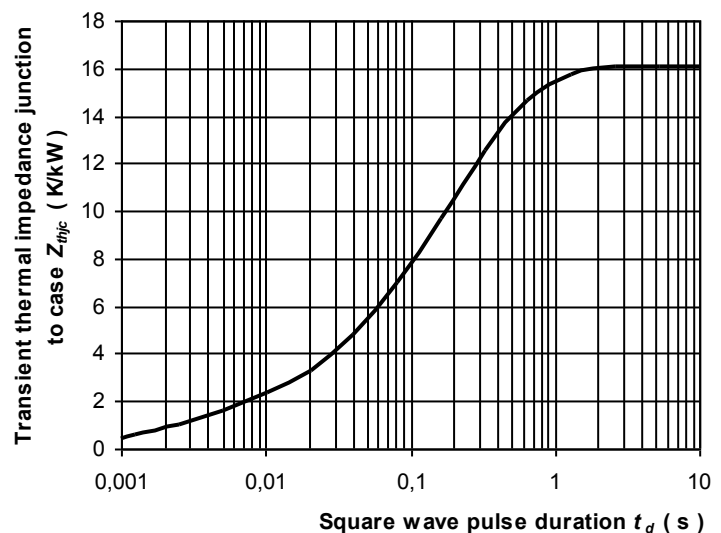


Fig. 2 Dependence transient thermal impedance junction to case on square pulse

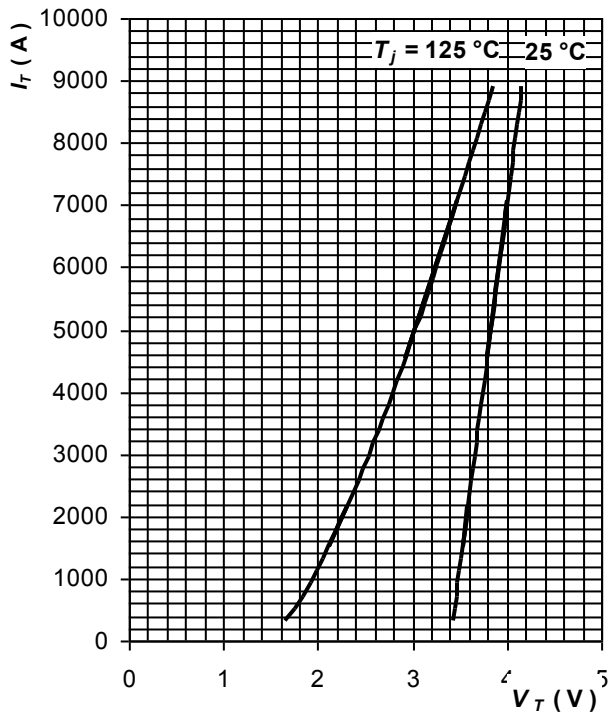


Fig. 3 Maximum on-state characteristics

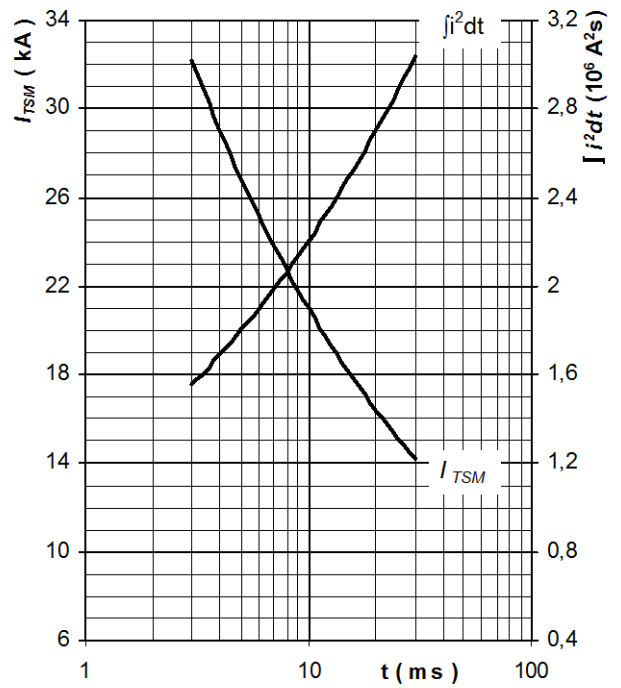


Fig. 4 Surge on-state current vs. pulse length, half sine wave, single pulse, $V_R = 0\text{ V}$, $T_j = T_{jmax}$

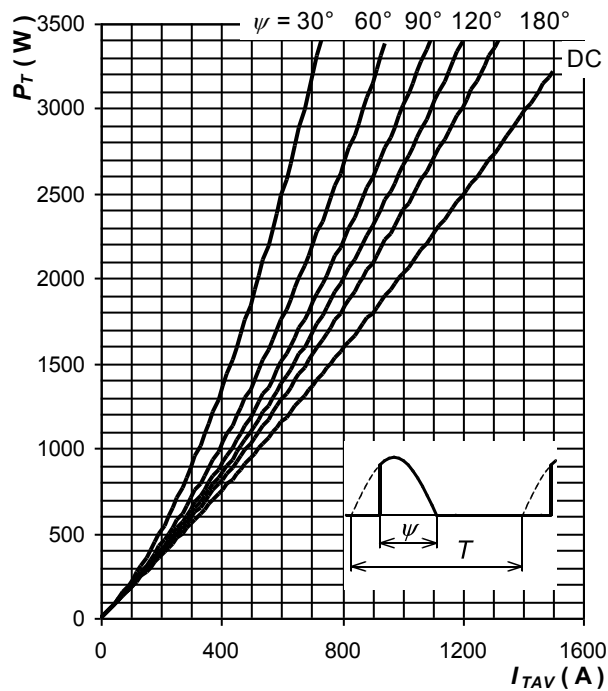


Fig. 5 On-state power loss vs. average on-state current, sine waveform, $f = 50\text{ Hz}$, $T = 1/f$

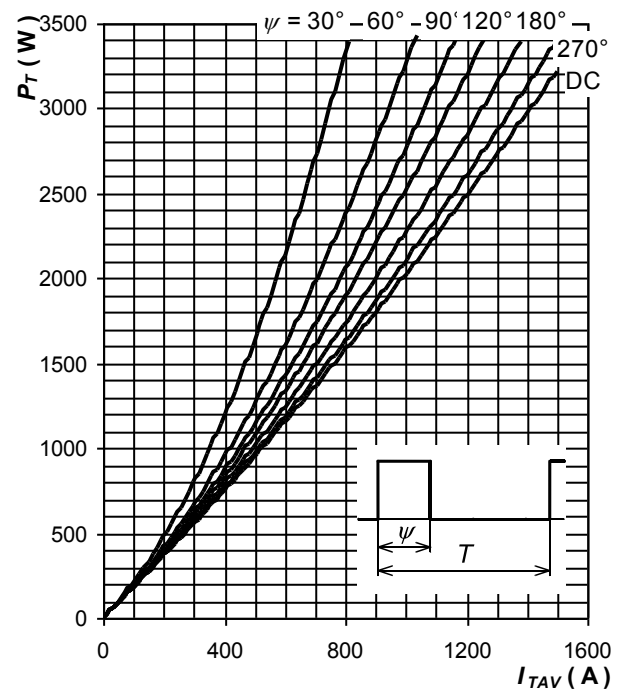


Fig. 6 On-state power loss vs. average on-state current, square waveform, $f = 50\text{ Hz}$, $T = 1/f$

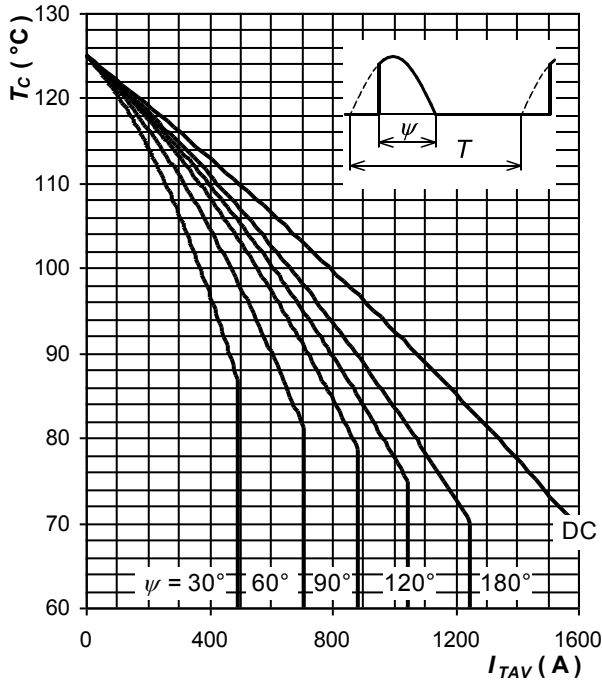


Fig. 7 Max. case temperature vs. aver. on-state current, sine waveform, $f = 50$ Hz, $T = 1/f$

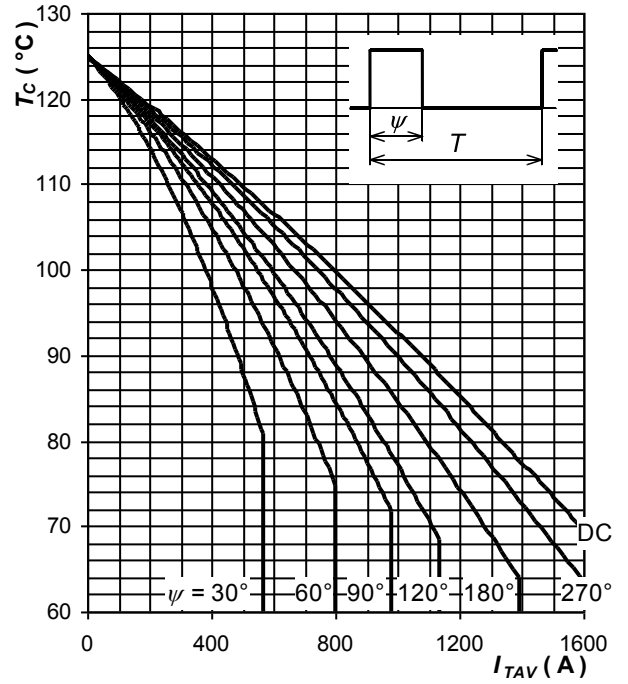


Fig. 8 Max. case temperature vs. aver. on-state current, square waveform, $f = 50$ Hz, $T = 1/f$

Notes: